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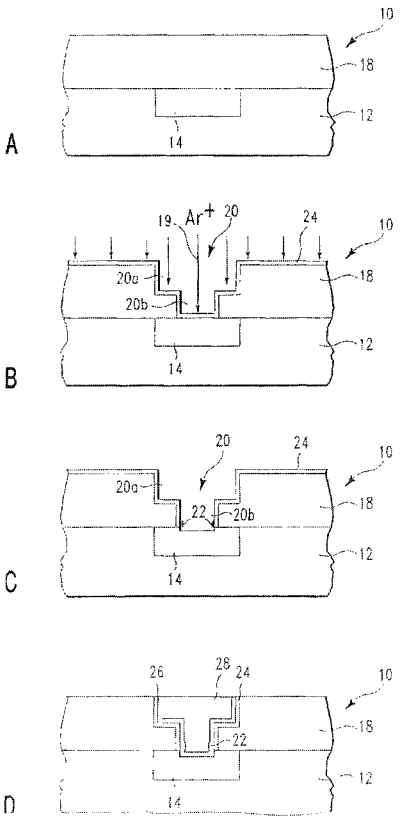
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(54) Title: A METHOD FOR DEPOSITING A METAL LAYER ON A SEMICONDUCTOR INTERCONNECT STRUCTURE



(57) Abstract: Disclosed is a method for depositing a metal layer on an interconnect structure for a semiconductor wafer. In the method, a metal conductor (14) is covered by a dielectric layer (18). The dielectric layer is patterned so as to expose the metal conductor. A liner layer (24) is then deposited into the pattern. The liner layer is then argon sputter etched to remove the liner layer and expose the metal conductor (14). In the process of argon sputter etching, the liner layer is redeposited onto the sidewall of the pattern. Lastly, an additional layer (26) is deposited into the pattern and covers the redeposited liner layer.

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